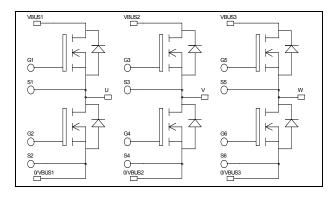


Triple phase leg <u>MOSFET Power Module</u>



 $V_{DSS} = 500V$ $R_{DSon} = 65m\Omega \text{ typ } @ \text{Tj} = 25^{\circ}\text{C}$ $I_D = 51A @ \text{Tc} = 25^{\circ}\text{C}$

Application

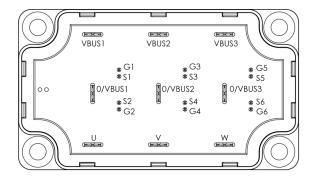
- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 7[®] FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration



- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a phase leg of three times the current capability
- Module can be configured as a three phase bridge
- Module can be configured as a boost followed by a full bridge
- RoHS Compliant



Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{ m DSS}$	Drain - Source Breakdown Voltage		500	V
т	Continuous Drain Current	$T_c = 25^{\circ}C$	51	
I_{D}		$T_c = 80$ °C	38	A
I_{DM}	Pulsed Drain current		204	
V_{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		78	mΩ
P_{D}	Maximum Power Dissipation $T_c = 25^{\circ}C$		390	W
I_{AR}	Avalanche current (repetitive and non repetitive)		51	A
E _{AR}	Repetitive Avalanche Energy		50	ma I
E_{AS}	Single Pulse Avalanche Energy		3000	mJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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All ratings @ $T_j = 25^{\circ}$ C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 500V$ $T_j = 25^{\circ}$	С		100	μА
		$V_{GS} = 0V, V_{DS} = 400V$ $T_j = 125$	°C		500	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 25.5A$		65	78	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 2.5 \text{mA}$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

Dynamic Characteristics

·	Characteristic	Test Conditions	Min	Тур	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		7000		
C_{oss}	Output Capacitance	$V_{DS} = 25V$		1400		pF
C_{rss}	Reverse Transfer Capacitance	f = 1MHz		90		
Q_{g}	Total gate Charge	$V_{GS} = 10V$		140		
Q_{gs}	Gate – Source Charge	$V_{\text{Bus}} = 250V$		40		nC
$Q_{gd} \\$	Gate – Drain Charge	$I_D = 51A$		70		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C		21		
T_{r}	Rise Time	$V_{GS} = 15V$		38		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 333V$ $I_{\text{D}} = 51A$		75		ns
T_{f}	Fall Time	$R_G = 3\Omega$		93		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		1035		
E_{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 51A, R_G = 3\Omega$		845		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C		1556		
E _{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 333V$ $I_D = 51A, R_G = 3\Omega$		1013		μJ

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I_S	Continuous Source current		$Tc = 25^{\circ}C$			51	Α.
	(Body diode)		$Tc = 80^{\circ}C$			38	Α
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -51A$	L			1.3	V
dv/dt	Peak Diode Recovery •					15	V/ns
	Payara Pagayary Time		$T_j = 25^{\circ}C$			270	12 G
t_{rr}	Reverse Recovery Time	$I_S = -51A$ $V_R = 333V$	$T_j = 125$ °C			540	ns
Qrr	Davana Dagayam, Changa	$di_S/dt = 100A/\mu s$	$T_j = 25$ °C		2.6		
	Reverse Recovery Charge	,	$T_j = 125$ °C		9.6		μC

• dv/dt numbers reflect the limitations of the circuit rather than the device itself.

 $I_S \le -51A$ $di/dt \le 700A/\mu s$ $V_R \le V_{DSS}$ $T_j \le 150$ °C

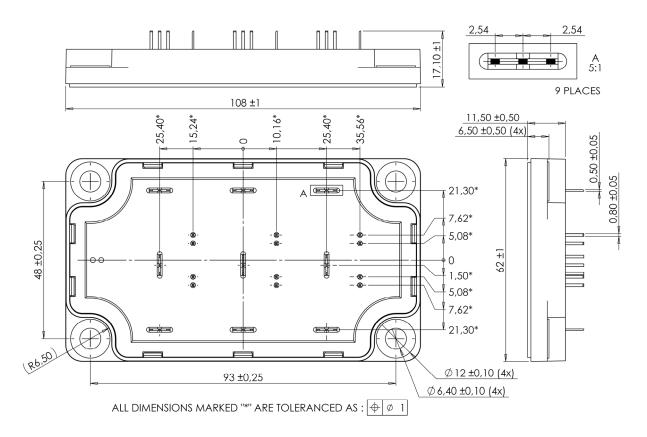
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Thermal and package characteristics

Symbol	Characteristic		Min	Тур	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.32	°C/W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		150	
T_{STG}	Storage Temperature Range			-40		125	°C
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Wt	Package Weight					250	g

SP6-P Package outline (dimensions in mm)

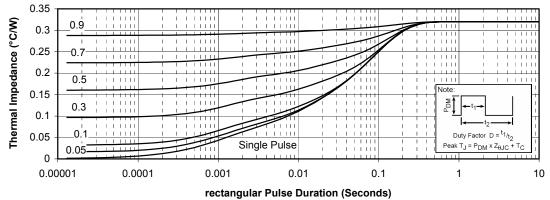


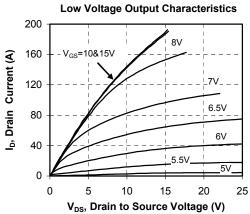
See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

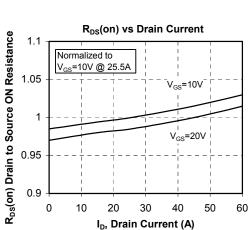


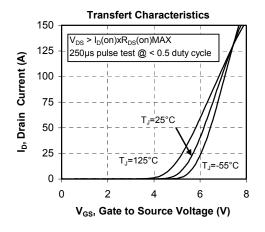
Typical Performance Curve

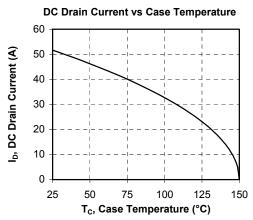
Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration







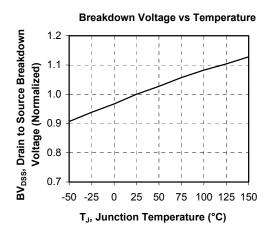


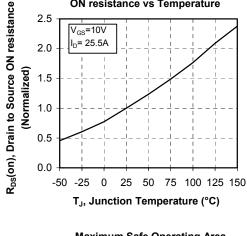


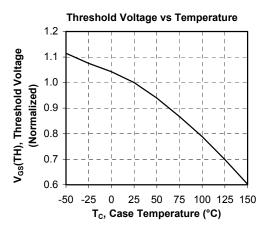
4 - 7

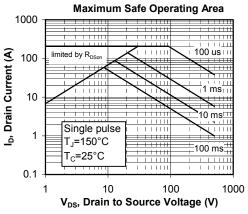


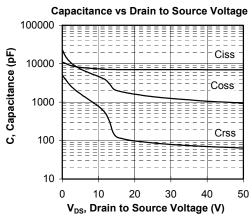
ON resistance vs Temperature

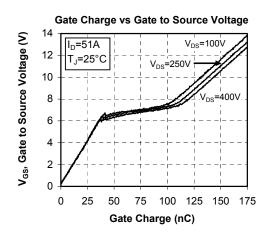




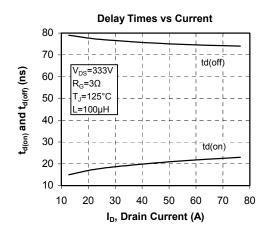


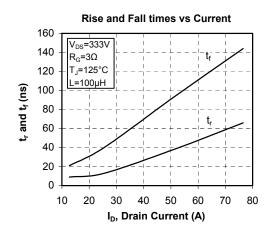


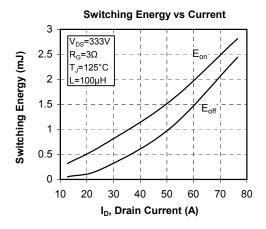


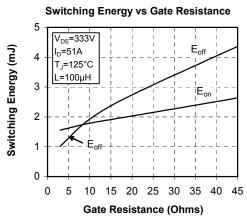


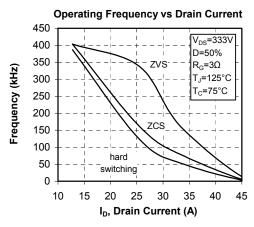


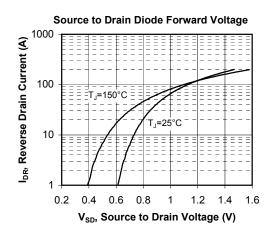












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